

TPAC1.1 progress

Jamie C

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Status

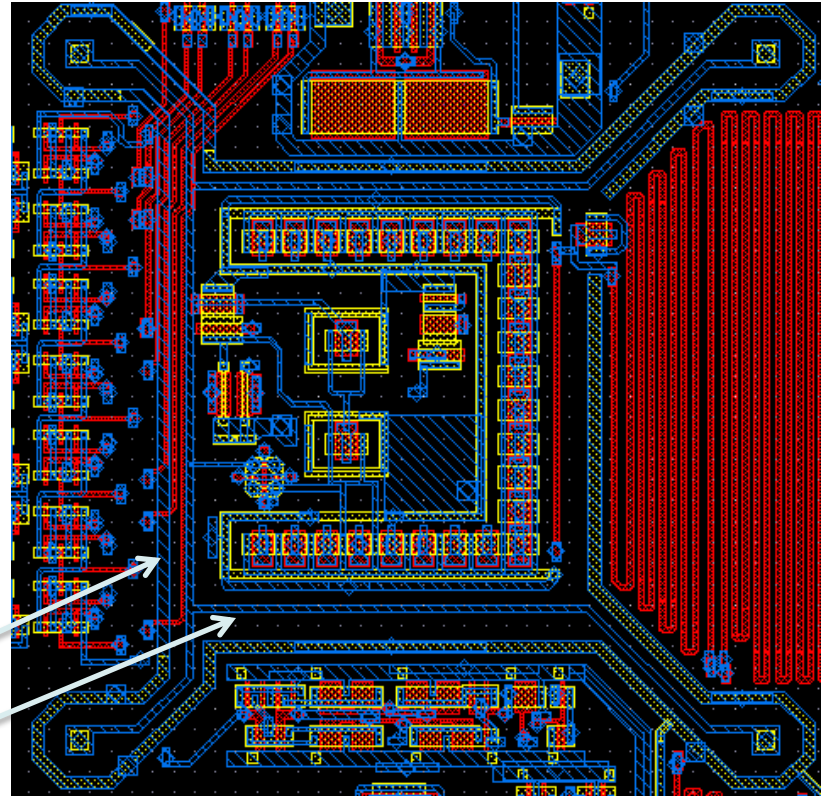
- FDR changes
 - Single variant ② implemented across all bulk pixels
 - Pixel layout changes as recommended
 - New resistor layout(s)
 - New test pixels - as 3x3 blocks of old/new shaper design
 - Larger bond pads
 - Assorted test devices to occupy spare pad sites
 - Changes for Hi-Res processing
- LVS & DRC
 - Top (without pads) ok, including 18 test pixels
- To do
 - Add test devices to top level schematic/layout
 - LVS including pad cells
 - Antenna checks
 - Auto-fill where necessary
 - DRC the DPW rules
 - Tape out/in & repeat all checks

Resistors (again)

- Now have a better understanding
 - Previous suspicions were unfounded...
 - In the calculation of resistance, the drawn width is adjusted by a $-\Delta W$ term which is large relative to our W : $\sim O(30\%)$
 - Some earlier versions of the tools incorrectly omitted this term, leading to incorrect resistance calculations and my subsequent misunderstanding
- Potential issue with resistor matching
 - Various contributing factors in processing
 - Foundry will send me some more data on variation of this ΔW term
 - Mismatch models probably don't account for variation of this term
 - Recommended minimum width makes this ΔW insignificant: $\sim O(3\%)$ but is impractical in the pixel.
 - Most likely cause of lower-than-expected gain in shapers, although the drawn geometry was actually ok
- Recommended action
 - Target 4Mohm (as original design) but use the larger available space to increase resistor width to improve potential issues with ΔW .
 - Can achieve 4.2Mohm with wider resistor, giving $\Delta W = \sim O(21\%)$
 - Test structure resistors of the old and new resistor that can be easily measured on each device for monitoring variance

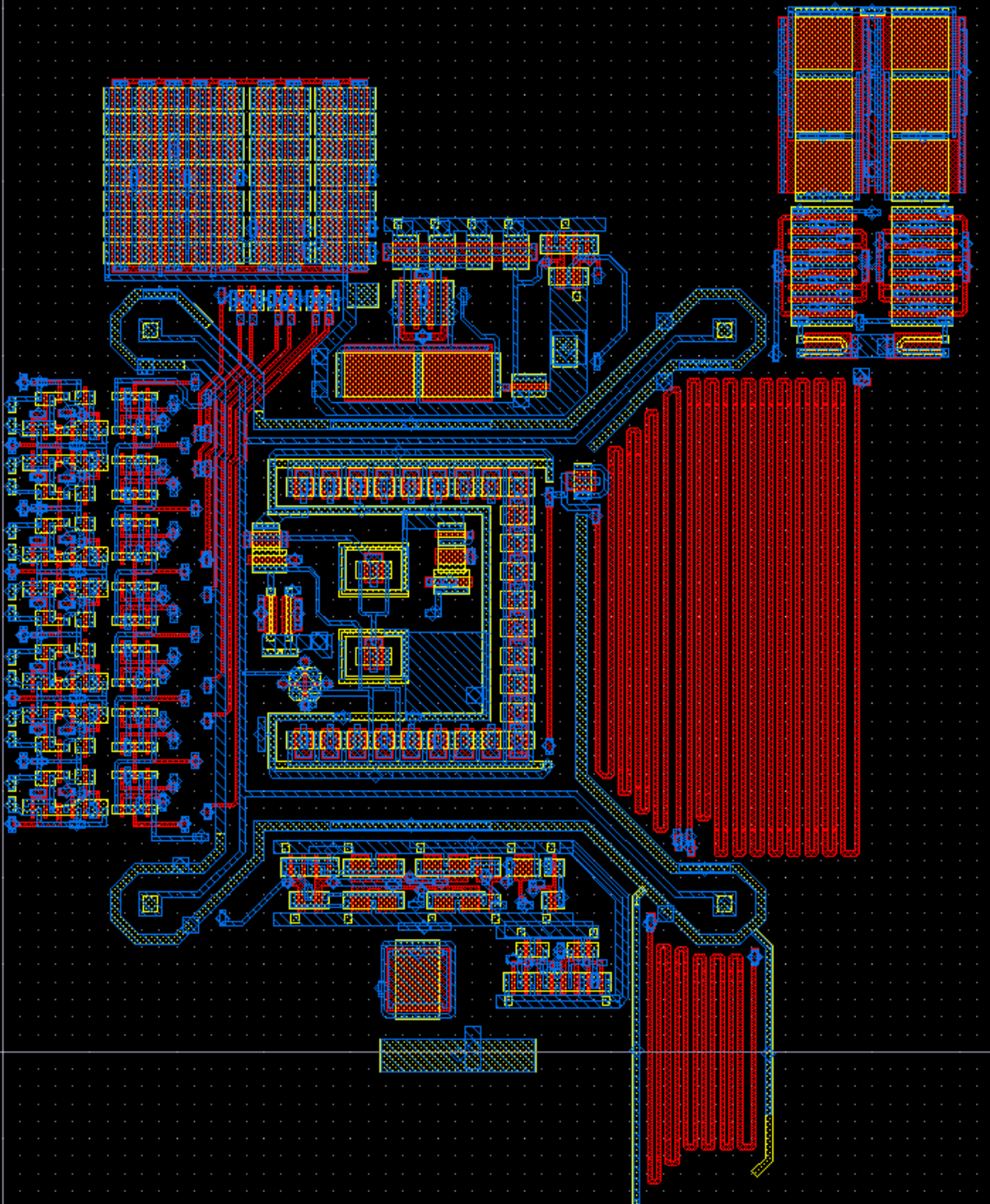
Parasitics in the pixel

- Reduced to $<$ original design
 - 13.7fF

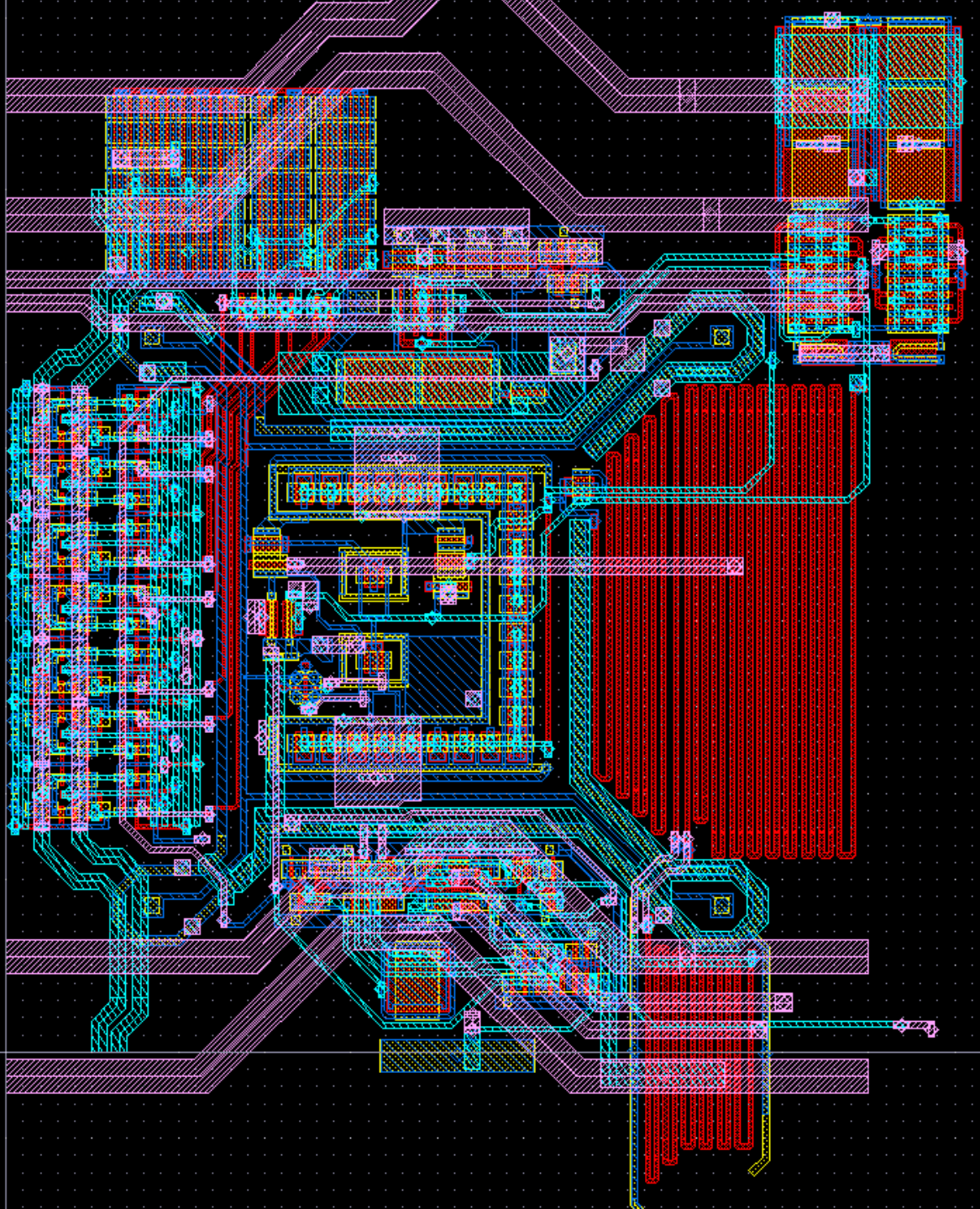


Guard ring \rightarrow diode node
separation increased where
possible

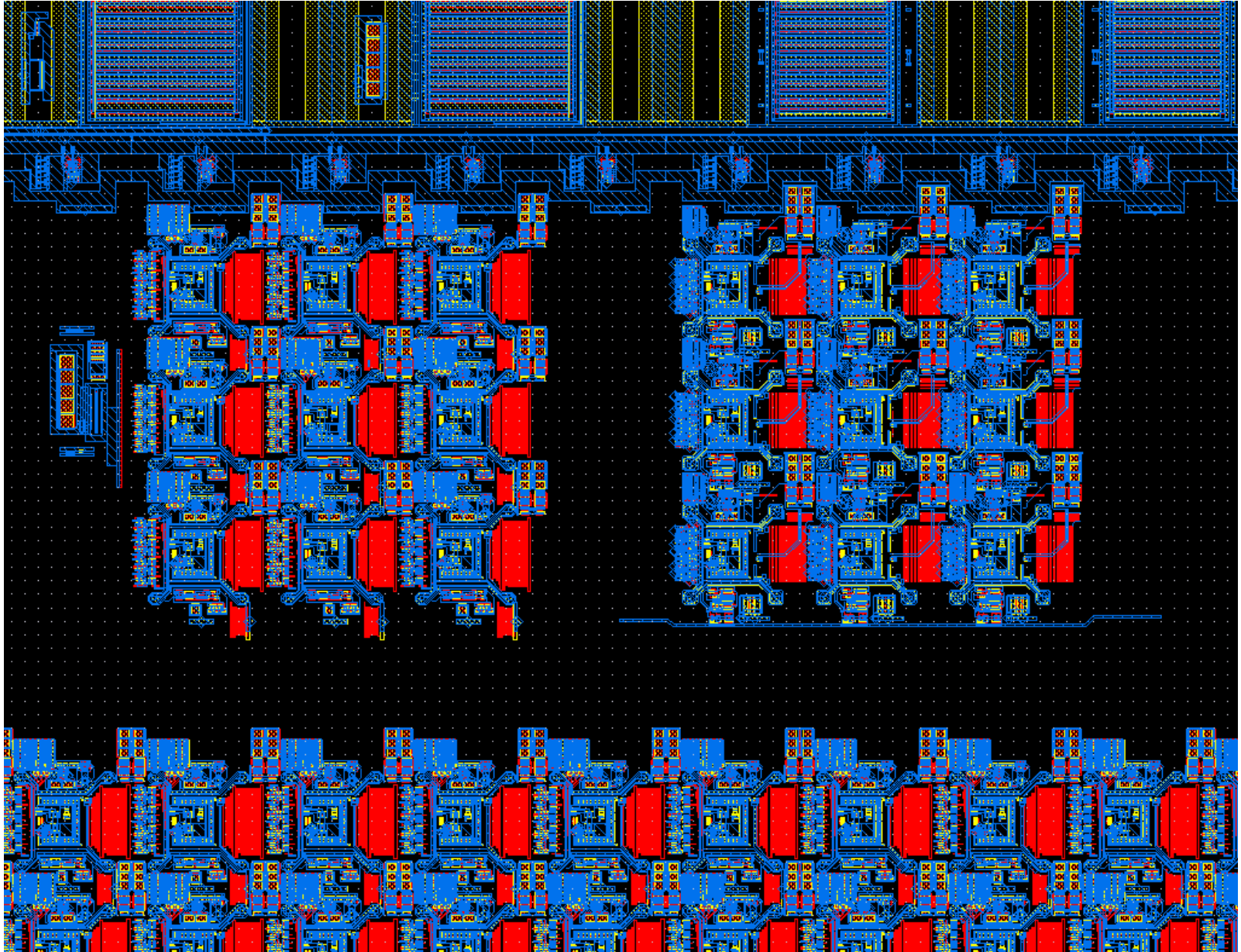
Pixel <M2



Pixel <M4



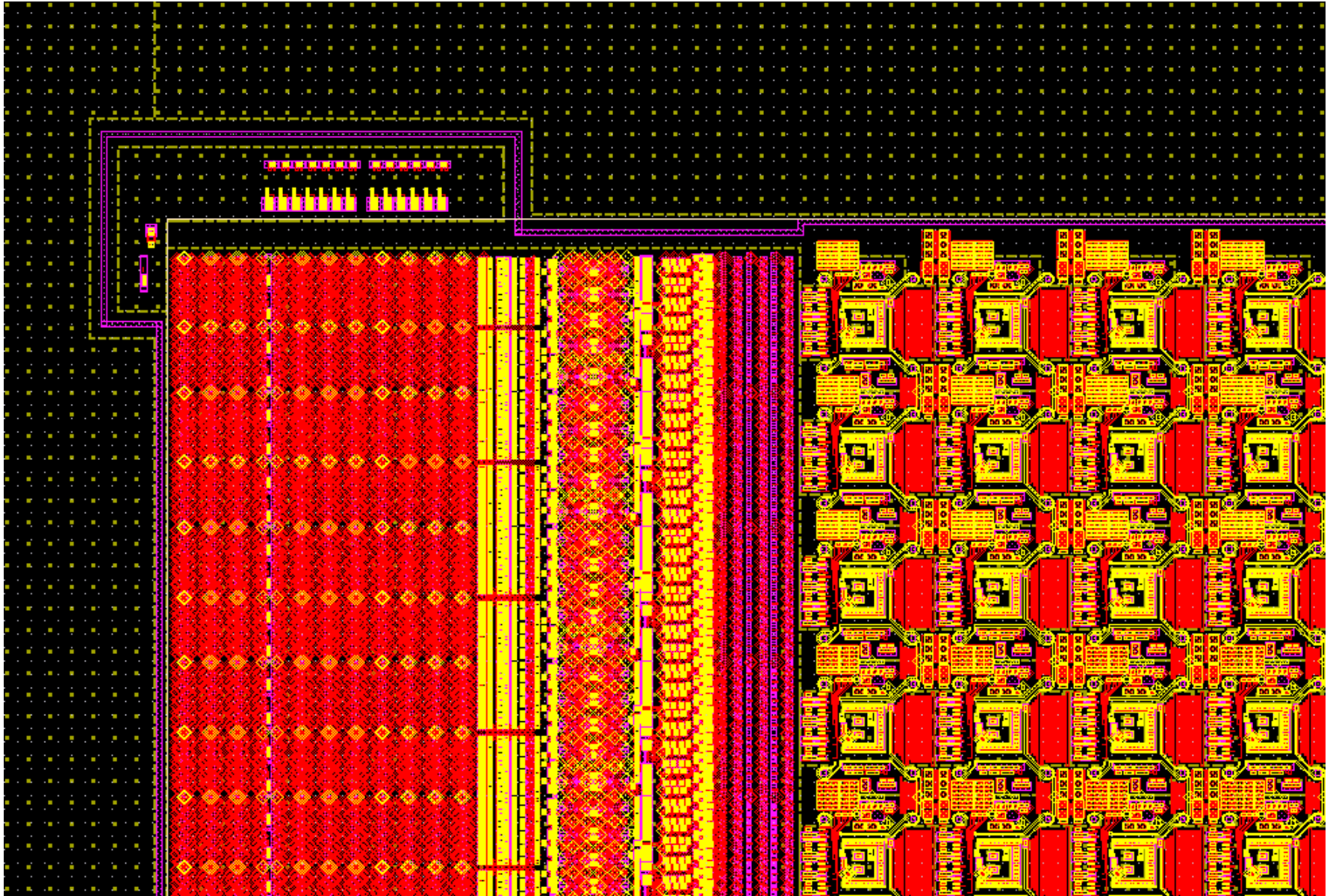
Test Pixels



Changes for Hi-Res Epi

- Placed a NWEELL guard ring around the bulk pixels
 - 2.1um wide constant track around bulk pixels & logic
 - Connected to old VRST pads for external drive
 - (jumper/dac on PCB)
 - Additional guard ring around test pixels
- Placed DPW everywhere except pixels

Guard ring: Example



Test structures

PADS

- Transistors
 - Nmos (lv/hv) for characterisation, noise measurement, based on unit cell based on input transistor in preShape pixel design 15
 - Pmos (lv/hv) for characterisation, noise measurement
 - Additional long device (TBC)
- Diodes
 - 1000 diodes for leakage current measurements 2
- Capacitors
 - O(1pF) made from the 1x1um pixel cells in parallel
 - O(0.5pF) made from parallel units of 2 series capacitors 3
- Nwell-Nwell isolation 3
- Resistors
 - Original 4M Ω 2
 - New wider 4.2M Ω
 - 2* 4M Ω resistors with larger widths to monitor matching/variance for future projects 5
- Foundry will place an extra strip of their standard PCM structures 0
 - One with, one without DPW
 - Will be tested as part of their standard procedure → immediate and directly comparable data for identical structures with/without DPW